

# **BUK7Y18-55B**

# N-channel TrenchMOS standard level FET Rev. 04 — 7 April 2010

**Product data sheet** 

### **Product profile**

#### 1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using Nexperia High-Performance Automotive (HPA) TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

#### 1.2 Features and benefits

- Q101 compliant
- Suitable for standard level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

#### 1.3 Applications

- 12 V and 24 V loads
- Advanced braking systems (ABS)
- Automotive systems

- Engine management
- General purpose power switching
- Motors, lamps and solenoids

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$	-	-	55	V
I <sub>D</sub>	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C};$ see <u>Figure 1</u> ; see <u>Figure 4</u>	-	-	47.4	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	-	85	W
Static chara	acteristics					
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 20 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 12}}{\text{see } \frac{\text{Figure 13}}{\text{Figure 13}}};$	-	12.7	18	mΩ
Avalanche	ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D = 47.4 \text{ A}; V_{sup} \le 55 \text{ V};$ $R_{GS} = 50 \Omega; V_{GS} = 10 \text{ V};$ $T_{j(init)} = 25 ^{\circ}\text{C}; \text{ unclamped}$	-	-	77	mJ
Dynamic ch	naracteristics					
$Q_{GD}$	gate-drain charge	$I_D = 20 \text{ A}; V_{DS} = 44 \text{ V};$ $V_{GS} = 10 \text{ V}; \text{ see } \frac{\text{Figure } 14}{\text{Figure } 14}$	-	8.1	-	nC



# 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		
2	S	source	mb	D
3	S	source		
4	G	gate		<u> </u>
mb	D	mounting base; connected to drain	1 2 3 4	mbb076 S
			SOT669 (LFPAK)	

# 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK7Y18-55B	LFPAK	plastic single-ended surface-mounted package (LFPAK); 4 leads	SOT669

# 4. Limiting values

Table 4. Limiting values

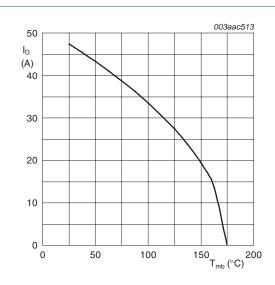
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	55	V
$V_{DGR}$	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$		-	-	55	V
$V_{GS}$	gate-source voltage			-20	-	20	V
I <sub>D</sub>	drain current	$T_{mb}$ = 25 °C; $V_{GS}$ = 10 V; see <u>Figure 1</u> ; see <u>Figure 4</u>		-	-	47.4	Α
		$T_{mb}$ = 100 °C; $V_{GS}$ = 10 V; see <u>Figure 1</u>		-	-	33.5	Α
I <sub>DM</sub>	peak drain current	$T_{mb}$ = 25 °C; $t_p \le 10 \mu s$ ; pulsed; see Figure 4		-	-	189	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	-	85	W
T <sub>stg</sub>	storage temperature			-55	-	175	°C
T <sub>j</sub>	junction temperature			-55	-	175	°C
Source-drain	n diode						
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C		-	-	47.4	Α
I <sub>SM</sub>	peak source current	$t_p \le 10 \mu\text{s}; \text{ pulsed}; T_{mb} = 25 ^{\circ}\text{C}$		-	-	189	Α
Avalanche ru	uggedness						
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D = 47.4 \text{ A; } V_{sup} \le 55 \text{ V; } R_{GS} = 50 \Omega;$ $V_{GS} = 10 \text{ V; } T_{j(init)} = 25 \text{ °C; unclamped}$		-	-	77	mJ
E <sub>DS(AL)R</sub>	repetitive drain-source avalanche energy	see Figure 3	[1][2][3]	-	-	-	J

<sup>[1]</sup> Single-pulse avalanche rating limited by maximum junction temperature of 175  $^{\circ}$ C.

<sup>[2]</sup> Repetitive avalanche rating limited by an average junction temperature of 170 °C.

<sup>[3]</sup> Refer to application note AN10273 for further information.



03na19 120 P<sub>der</sub> (%) 80 40 0 \_ 100 150 T<sub>mb</sub> (°C)  $P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$ 

Continuous drain current as a function of mounting base temperature

Normalized total power dissipation as a Fig 2. function of mounting base temperature

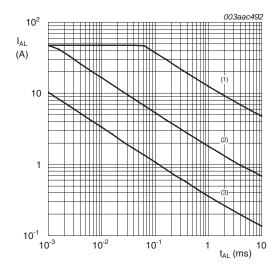
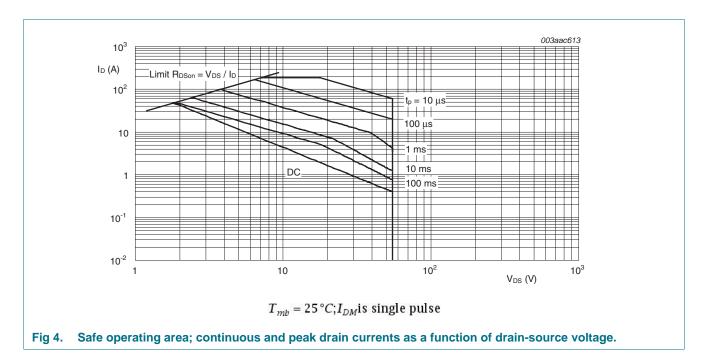


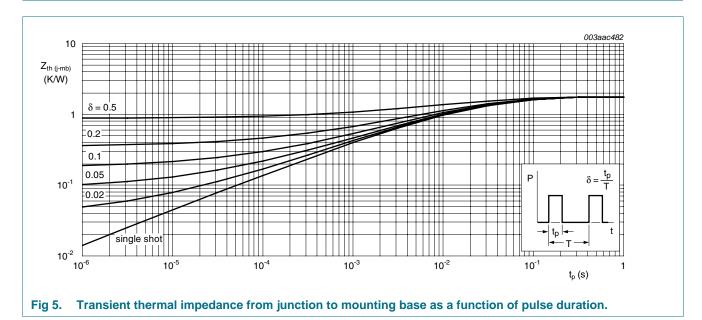
Fig 3. Single-pulse and repetitive avalanche rating; avalanche current as a function of avalanche time



### 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 5	-	-	1.76	K/W



# 6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V <sub>(BR)DSS</sub>	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	55	-	-	V
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	50	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}$ ; $V_{DS} = V_{GS}$ ; $T_j = 25 \text{ °C}$ ; see <u>Figure 10</u> ; see <u>Figure 11</u>	2	3	4	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = -55$ °C; see <u>Figure 10</u>	-	-	4.4	V
		$I_D = 1 \text{ mA}$ ; $V_{DS} = V_{GS}$ ; $T_j = 175 \text{ °C}$ ; see Figure 10	1	-	-	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	1	μΑ
		$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{DS} = 0 \text{ V}; V_{GS} = 20 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nΑ
		$V_{DS} = 0 \text{ V}; V_{GS} = -20 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nΑ
R <sub>DSon</sub> drain-source resistance	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 20 \text{ A}; T_j = 175 °C;$ see <u>Figure 12</u>	-	-	37.8	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 20 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 12; see Figure 13	-	12.7	18	mΩ
Dynamic	characteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 20 \text{ A}; V_{DS} = 44 \text{ V}; V_{GS} = 10 \text{ V};$	-	21.9	-	nC
Q <sub>GS</sub>	gate-source charge	see Figure 14	-	4.64	-	nC
$Q_{GD}$	gate-drain charge		-	8.1	-	nC
C <sub>iss</sub>	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$	-	947	1263	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 15</u>	-	223	268	pF
C <sub>rss</sub>	reverse transfer capacitance		-	105	144	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.5 \Omega; V_{GS} = 10 \text{ V};$	-	13	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 10 \Omega$	-	20	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	34	-	ns
t <sub>f</sub>	fall time		-	16	-	ns
Source-d	rain diode					
$V_{SD}$	source-drain voltage	$I_S = 20 \text{ A}$ ; $V_{GS} = 25 \text{ V}$ ; $T_j = 25 \text{ °C}$ ; see <u>Figure 16</u>	-	0.85	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 20 \text{ A}$ ; $dI_S/dt = -100 \text{ A/}\mu\text{s}$ ; $V_{GS} = 0 \text{ V}$ ;	-	36	-	ns
Q <sub>r</sub>	recovered charge	$V_{DS} = 30 \text{ V}$	-	55	-	nC

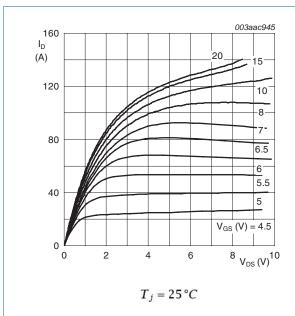


Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values.

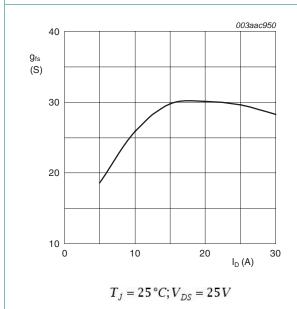


Fig 8. Forward transconductance as a function of drain current; typical values.

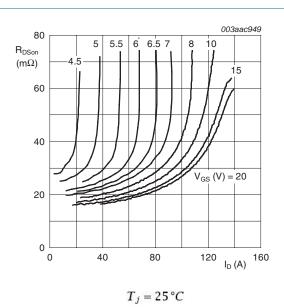
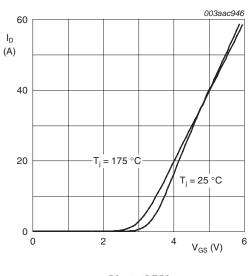
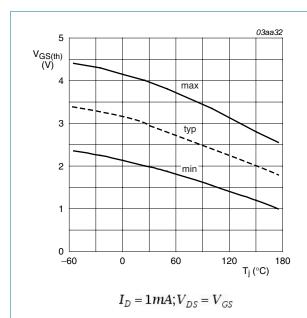


Fig 7. Drain-source on-state resistance as a function of drain current; typical values.



 $V_{DS} = 25V$ 

Fig 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values.



junction temperature

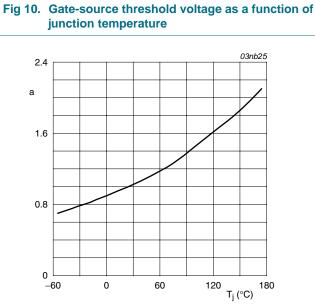
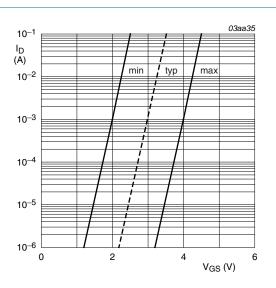
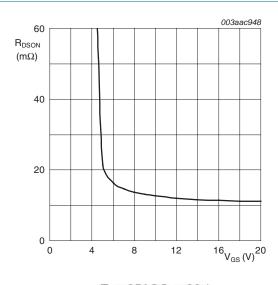


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature



$$T_j = 25 \,^{\circ}C; V_{DS} = 5V$$

Fig 11. Sub-threshold drain current as a function of gate-source voltage



 $T_j = 25 \,^{\circ}C; I_D = 20A$ 

Fig 13. Drain-source on-state resistance as a function of gate-source voltage; typical values.

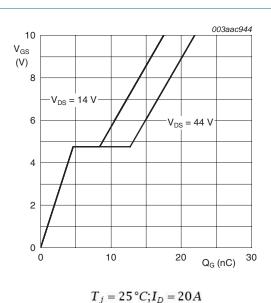
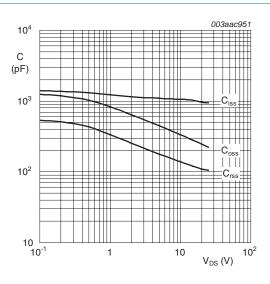


Fig 14. Gate-source voltage as a function of gate charge; typical values.



 $V_{GS} = 0V; f = 1MHz$ 

Fig 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values.

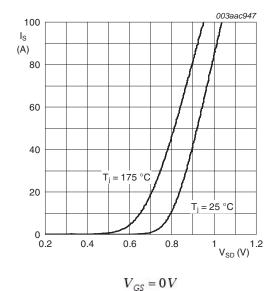
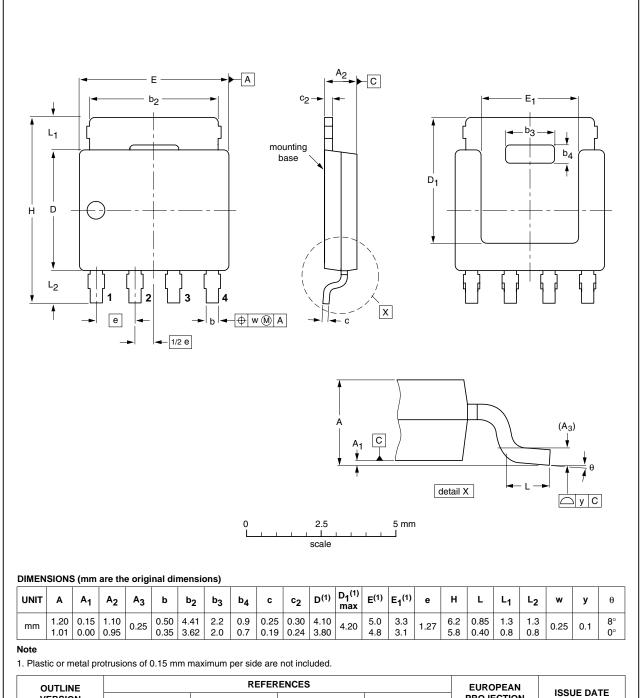


Fig 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values.

## 7. Package outline

### Plastic single-ended surface-mounted package (LFPAK); 4 leads

**SOT669** 



OUTLINE		REFER	ENCES	EUROPEAN		
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE	
SOT669		MO-235			<del>04-10-13</del> 06-03-16	

Fig 17. Package outline SOT669 (LFPAK)

BUK7Y18-55B

# 8. Revision history

#### Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK7Y18-55B_4	20100407	Product data sheet	-	BUK7Y18-55B_3
Modifications:	<ul> <li>Status char</li> </ul>	nged from objective to pro	oduct.	
BUK7Y18-55B_3	20100218	Objective data sheet	-	BUK7Y18-55B_2

### 9. Legal information

#### 9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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